



STx42N65M5

N-channel 650 V, 0.070 Ω , 33 A MDmesh™ V Power MOSFET
in I²PAK, TO-220, TO-220FP, D²PAK and TO-247

Features

Type	V _{DSS} @ T _{Jmax}	R _{DS(on)} max	I _D
STB42N65M5	710 V	< 0.079 Ω	33 A
STF42N65M5	710 V	< 0.079 Ω	33 A ⁽¹⁾
STI42N65M5	710 V	< 0.079 Ω	33 A
STP42N65M5	710 V	< 0.079 Ω	33 A
STW42N65M5	710 V	< 0.079 Ω	33 A

1. Limited only by maximum temperature allowed

- TO-220 worldwide best R_{DS(on)}
- Higher V_{DSS} rating
- High dv/dt capability
- Excellent switching performance
- Easy to drive
- 100% avalanche tested

Application

- Switching applications

Description

MDmesh™ V is a revolutionary Power MOSFET technology based on an innovative proprietary vertical process, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiencies.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB42N65M5	42N65M5	D ² PAK	Tape and reel
STF42N65M5	42N65M5	TO-220FP	Tube
STI42N65M5	42N65M5	I ² PAK	Tube
STP42N65M5	42N65M5	TO-220	Tube
STW42N65M5	42N65M5	TO-247	Tube

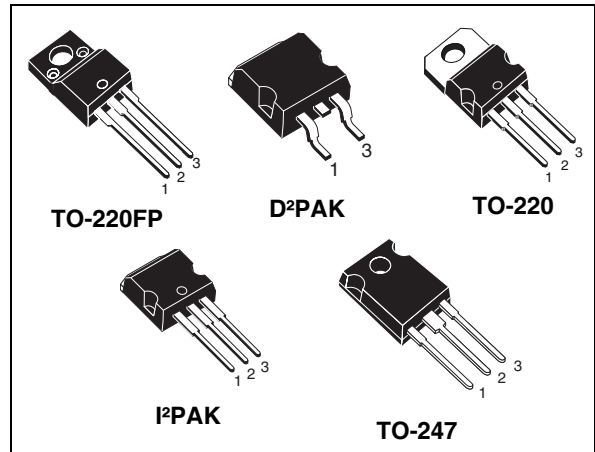
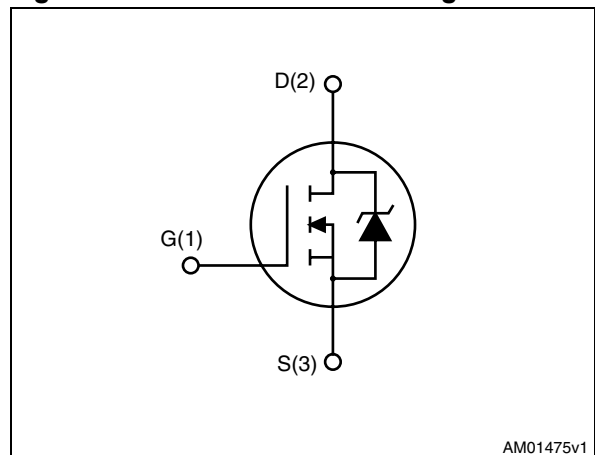


Figure 1. Internal schematic diagram



AM01475v1

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-220, TO-247 D ² PAK, I ² PAK	TO-220FP	
V _{GS}	Gate- source voltage	± 25		V
I _D	Drain current (continuous) at T _C = 25 °C	33	33 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	20.8	20.8 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	132	132 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	190	40	W
I _{AR}	Max current during repetitive or single pulse avalanche (pulse width limited by T _{JMAX})	11		A
E _{AS}	Single pulse avalanche energy (starting T _J = 25°C, I _D = I _{AR} , V _{DD} = 50V)	950		mJ
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15		V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)	--	2500	V
T _{stg}	Storage temperature	-55 to 150		°C
T _j	Max. operating junction temperature	150		°C

1. Limited only by maximum temperature allowed
2. Pulse width limited by safe operating area
3. I_{SD} ≤ 33 A, di/dt ≤ 400 A/μs, V_{Peak} < V_{(BR)DSS}

Table 3. Thermal data

Symbol	Parameter	Value					Unit
		D ² PAK	I ² PAK	TO-220	TO-247	TO-220FP	
R _{thj-case}	Thermal resistance junction-case max	0.66				3.1	°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	--	62.5	50	62.5		°C/W
R _{thj-pcb}	Thermal resistance junction-pcb max	30	--	--	--	--	°C/W
T _I	Maximum lead temperature for soldering purpose	300					°C

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}$, $T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 16.5\text{ A}$		0.070	0.079	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	4650 110 3.2	-	pF pF pF
$C_{o(er)}^{(1)}$	Equivalent output capacitance energy related	$V_{GS} = 0$, $V_{DS} = 0$ to 80% $V_{(BR)DSS}$	-	100	-	pF
$C_{o(tr)}^{(2)}$	Equivalent output capacitance time related	$V_{GS} = 0$, $V_{DS} = 0$ to 80% $V_{(BR)DSS}$	-	285	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.1	-	Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 520\text{ V}$, $I_D = 16.5\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 20)	-	100 26 38	-	nC nC nC

1. $C_{o(er)}$ is a constant capacitance value that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}
2. $C_{o(tr)}$ is a constant capacitance value that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 20\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 19)	-	61	-	ns
t_r	Rise time			24		ns
$t_{d(off)}$	Turn-off-delay time			65		ns
t_f	Fall time			13		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		33	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				132	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 33\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 33\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 24)	-	400		ns
Q_{rr}	Reverse recovery charge			7		μC
I_{RRM}	Reverse recovery current			35		A
t_{rr}	Reverse recovery time	$I_{SD} = 33\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 24)	-	532		ns
Q_{rr}	Reverse recovery charge			10		μC
I_{RRM}	Reverse recovery current			38		A

1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK, I²PAK

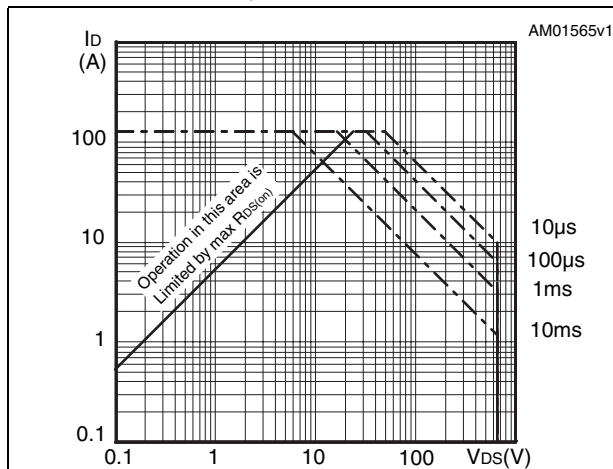


Figure 3. Thermal impedance for TO-220, D²PAK, I²PAK

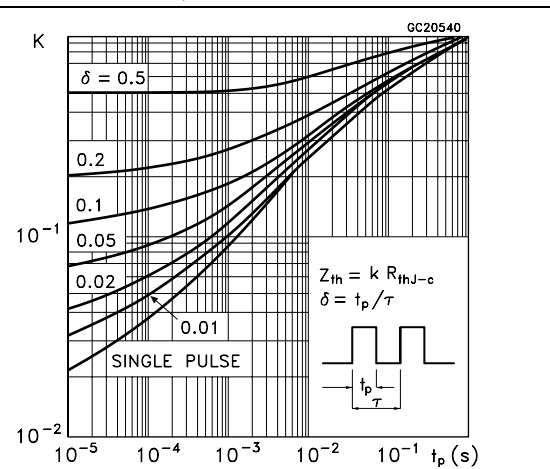


Figure 4. Safe operating area for TO-247

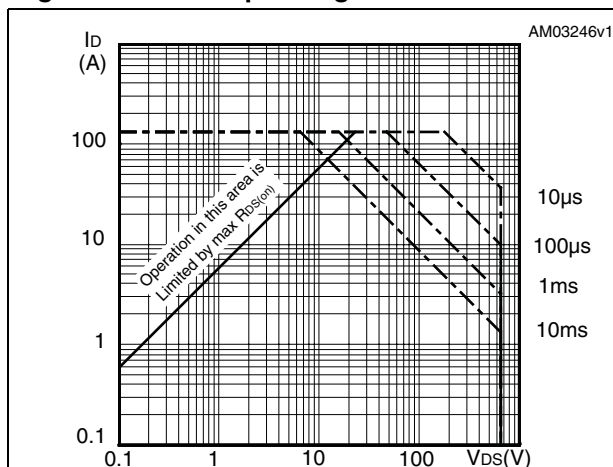


Figure 5. Thermal impedance for TO-247

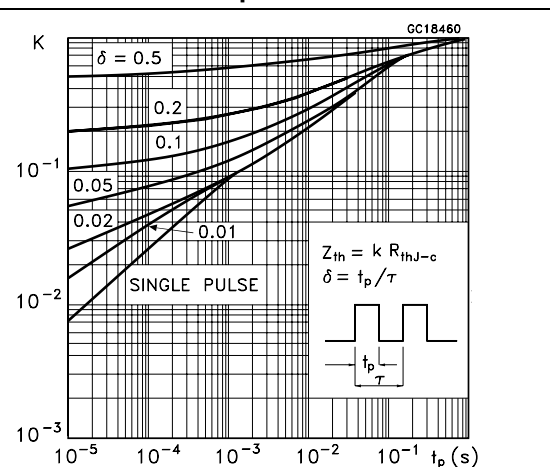


Figure 6. Safe operating area for TO-220FP

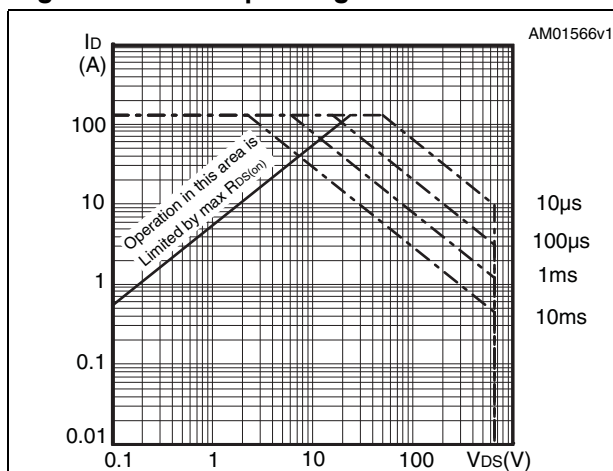


Figure 7. Thermal impedance for TO-220FP

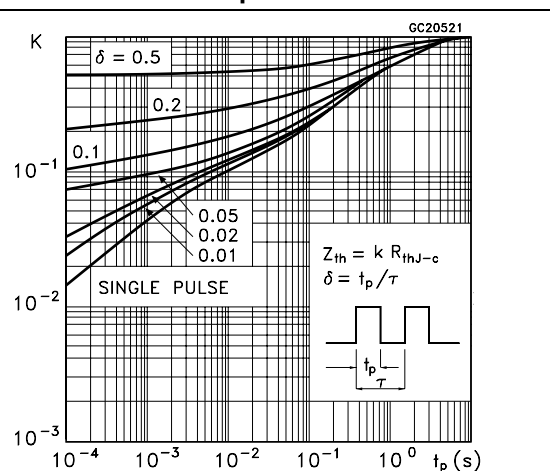


Figure 8. Output characteristics

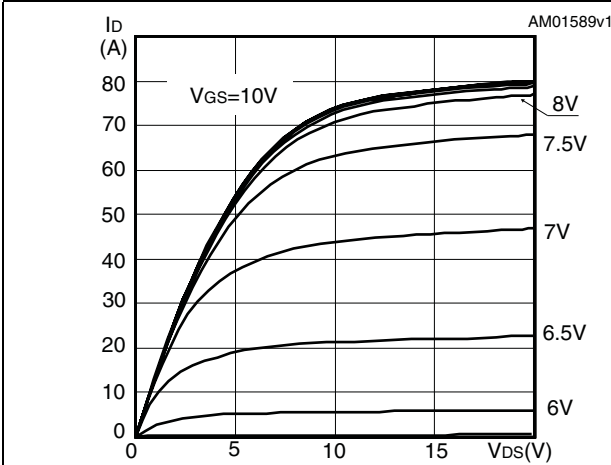


Figure 9. Transfer characteristics

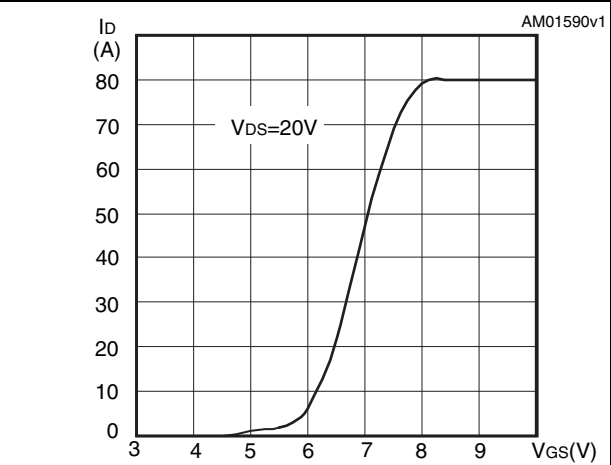


Figure 10. Gate charge vs gate-source voltage

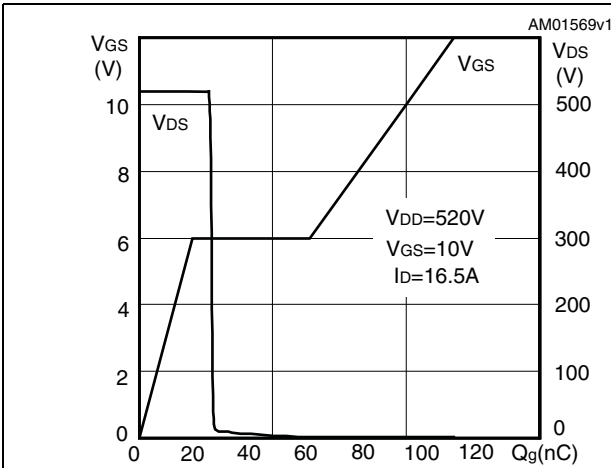


Figure 11. Static drain-source on resistance

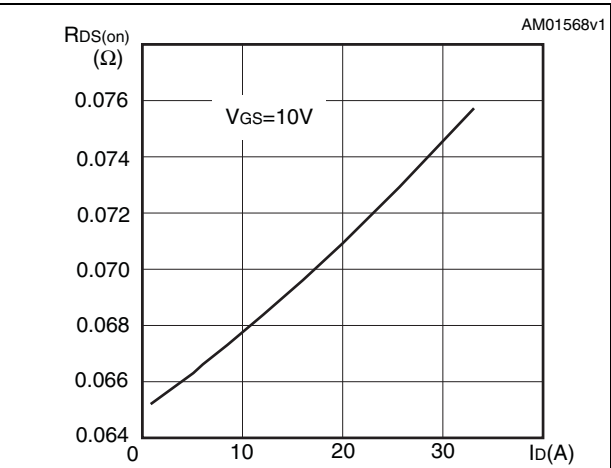


Figure 12. Capacitance variations

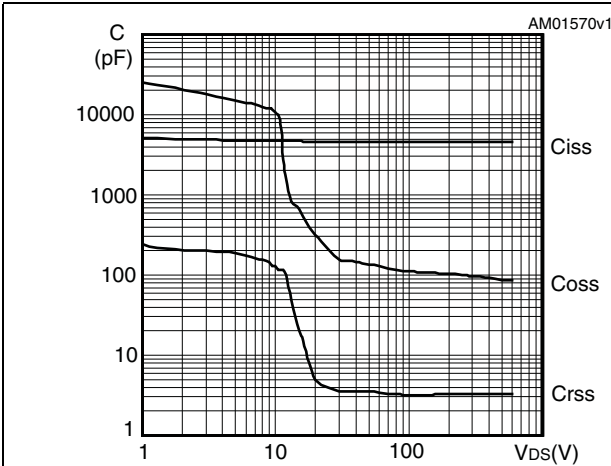


Figure 13. Output capacitance stored energy

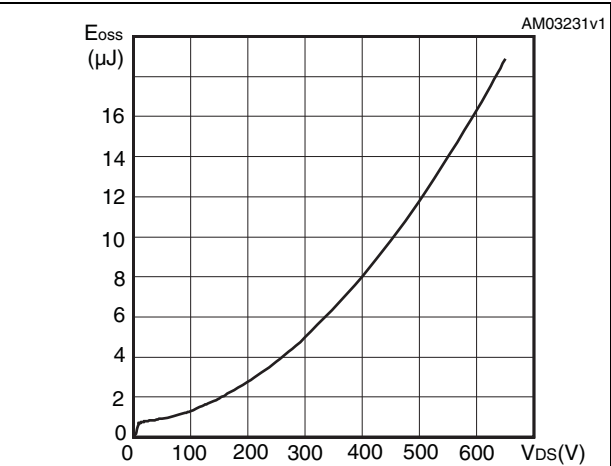


Figure 14. Normalized gate threshold voltage vs temperature

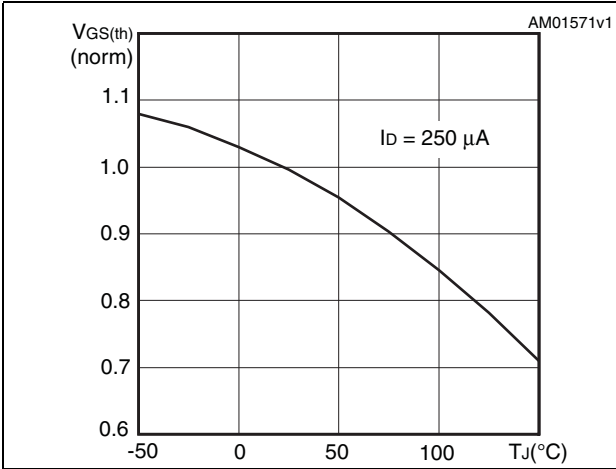


Figure 15. Normalized on resistance vs temperature

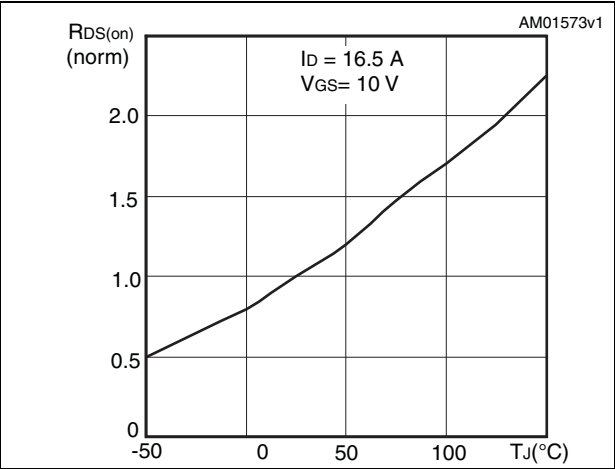


Figure 16. Source-drain diode forward characteristics

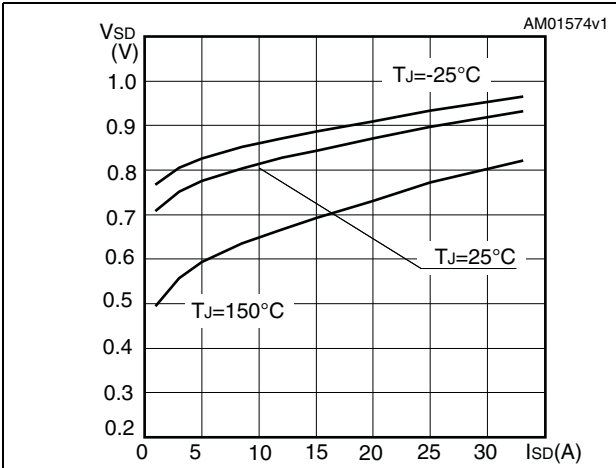


Figure 17. Normalized B_{VDSS} vs temperature

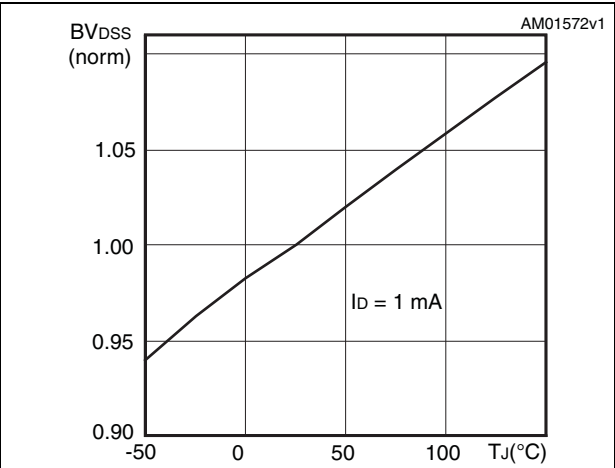
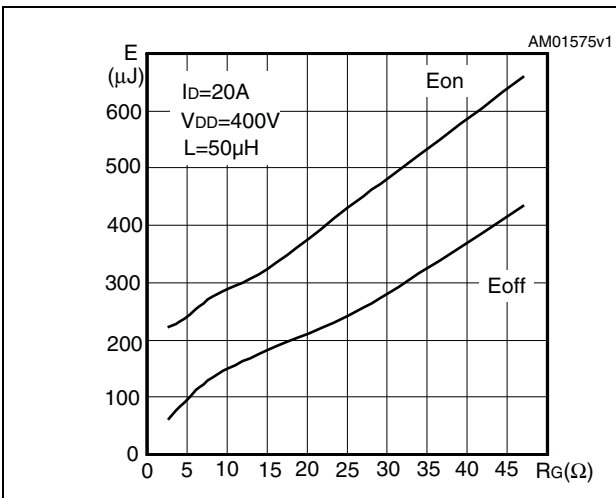


Figure 18. Switching losses vs gate resistance (1)



1. E_{on} including reverse recovery of a SiC diode

3 Test circuits

Figure 19. Switching times test circuit for resistive load

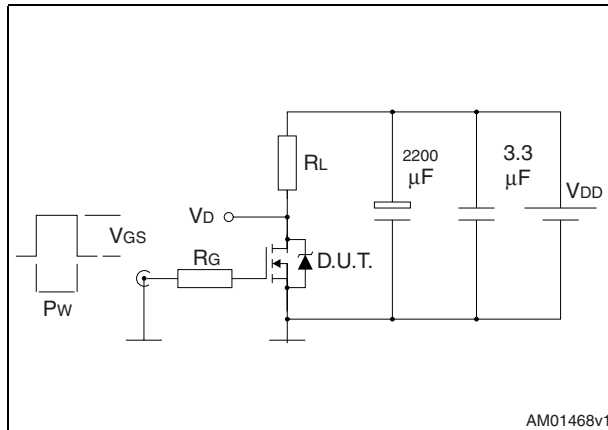


Figure 20. Gate charge test circuit

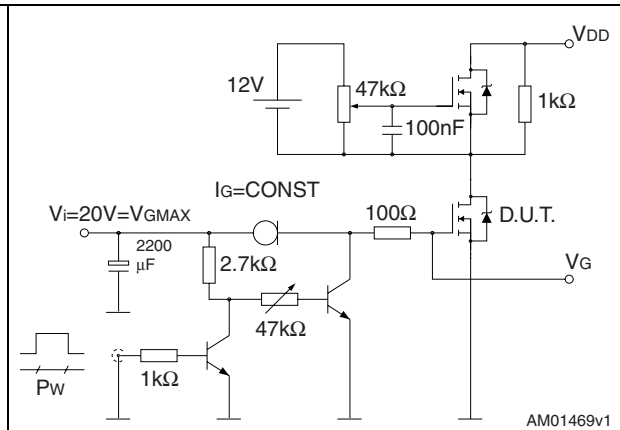


Figure 21. Test circuit for inductive load switching and diode recovery times

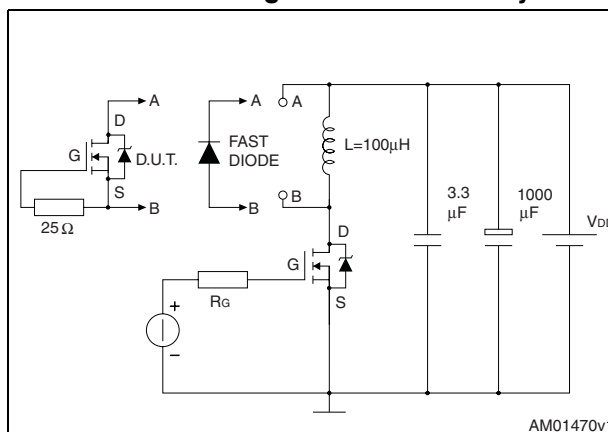


Figure 22. Unclamped inductive load test circuit

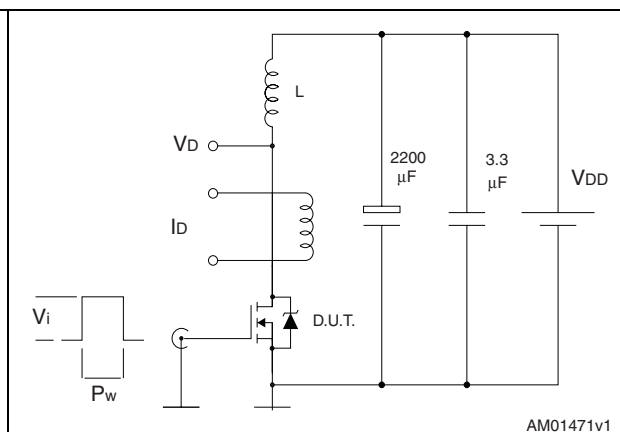


Figure 23. Unclamped inductive waveform

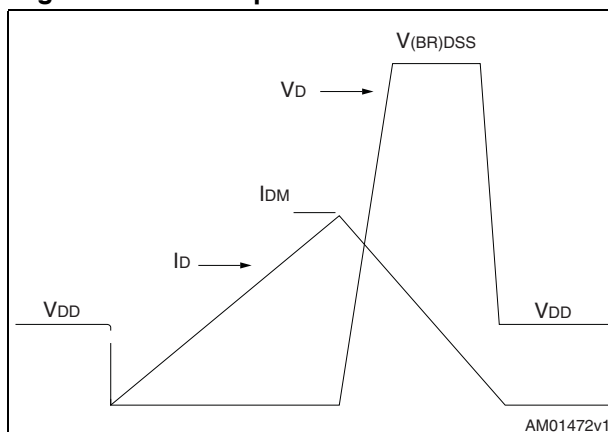
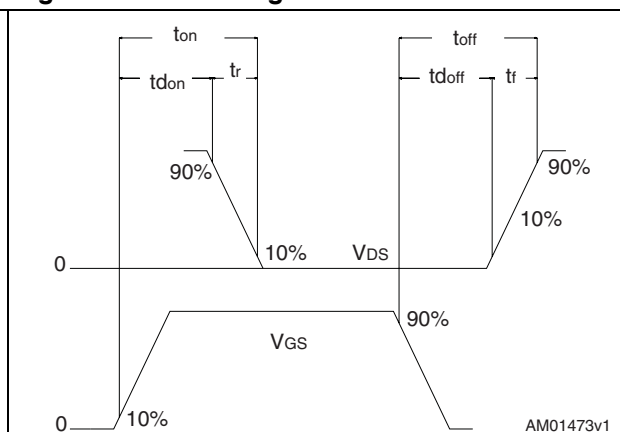


Figure 24. Switching time waveform

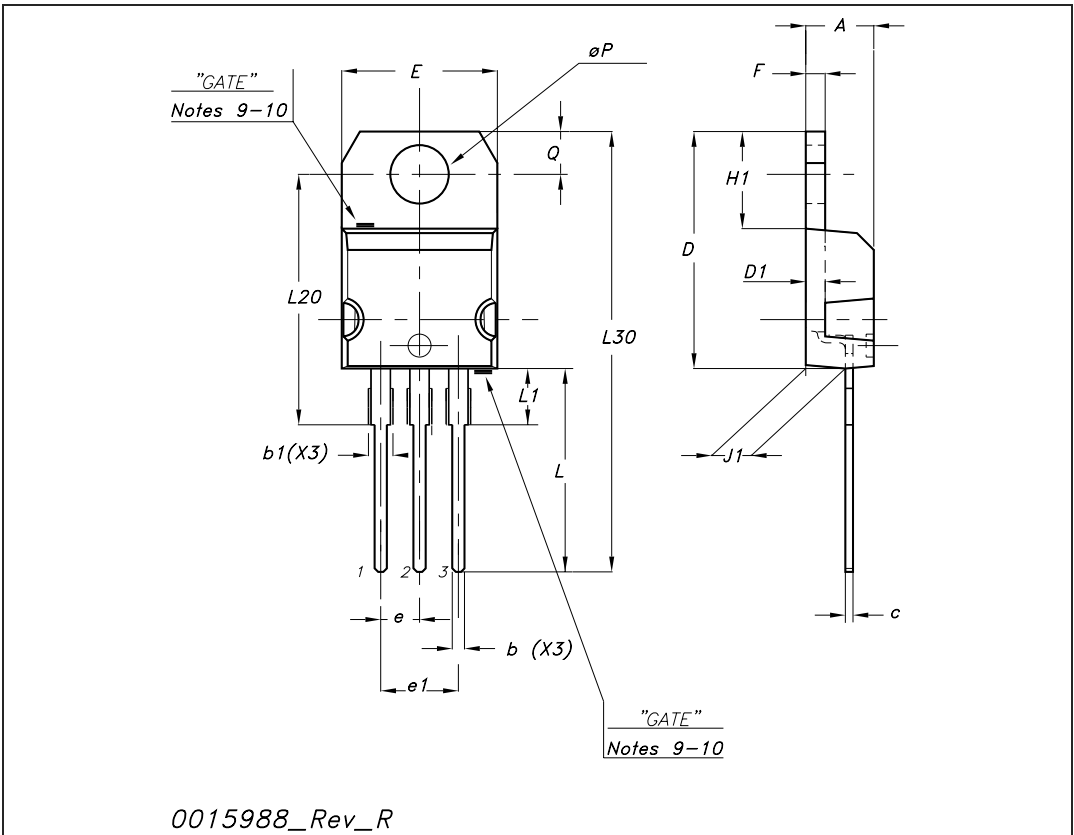


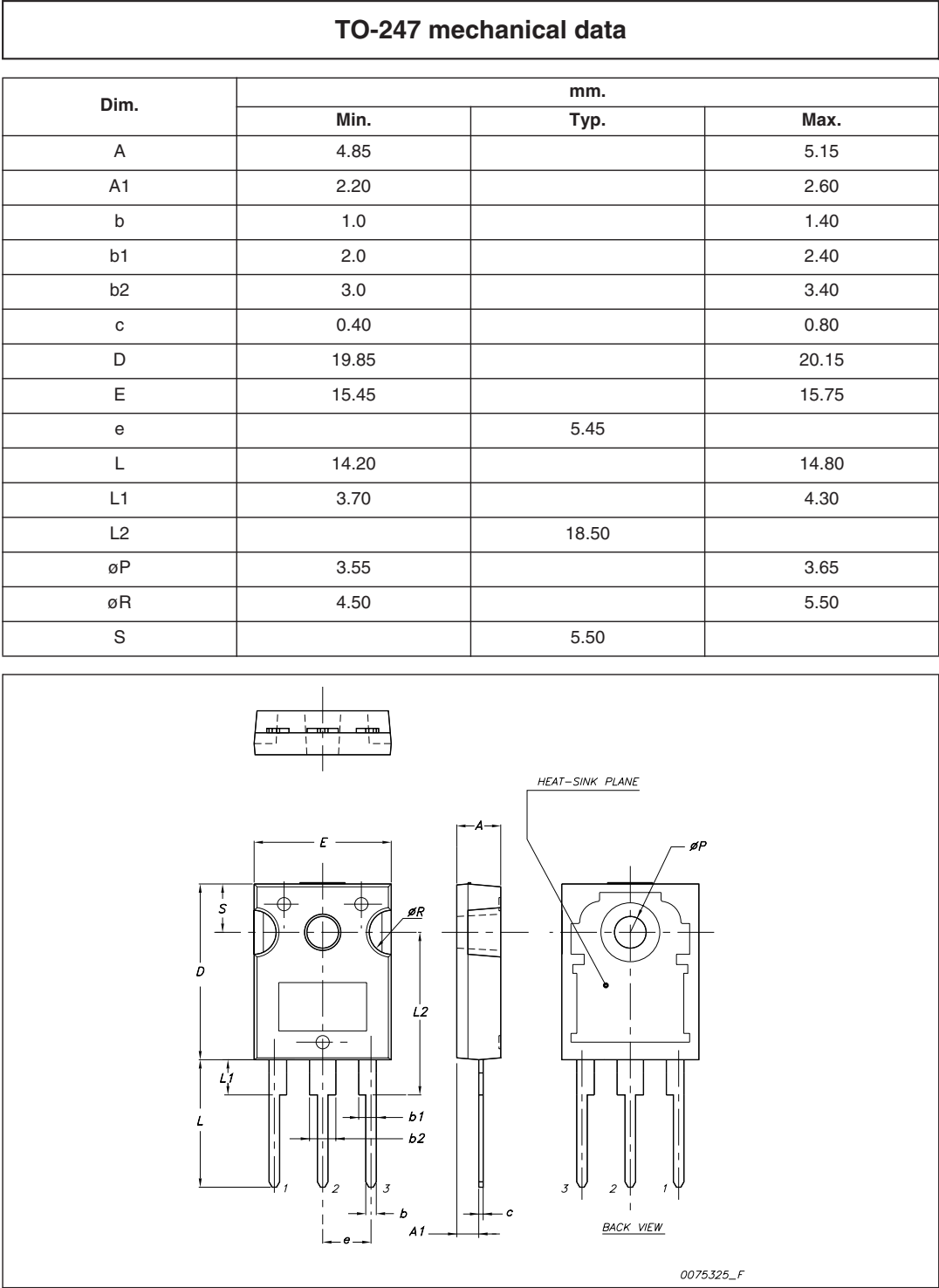
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

TO-220 mechanical data

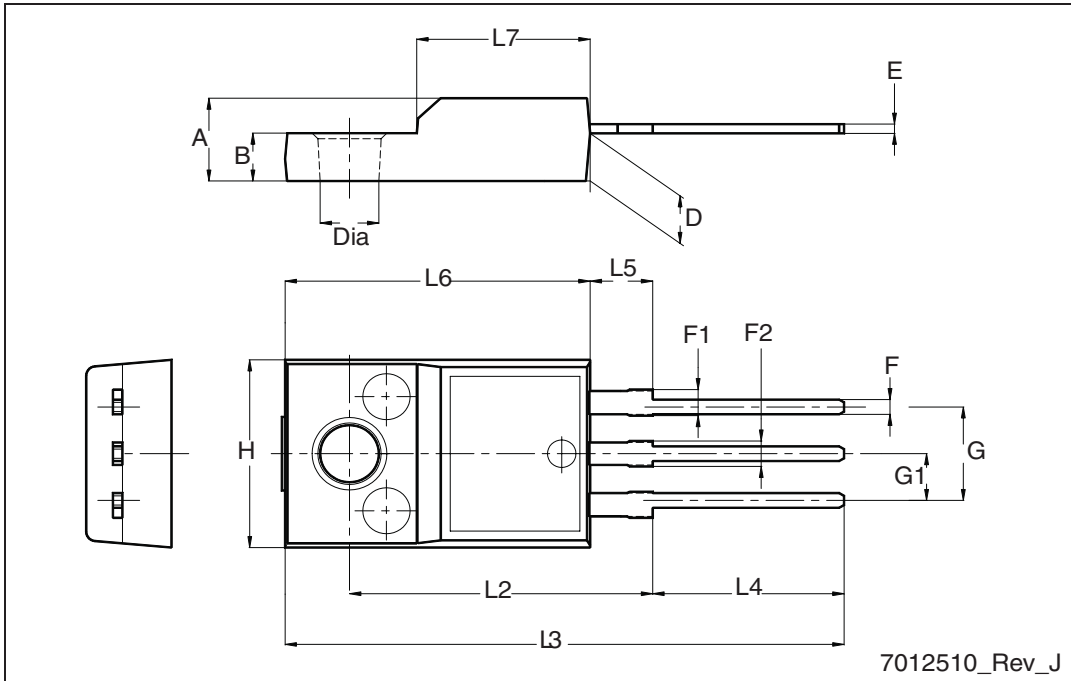
Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
ØP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116





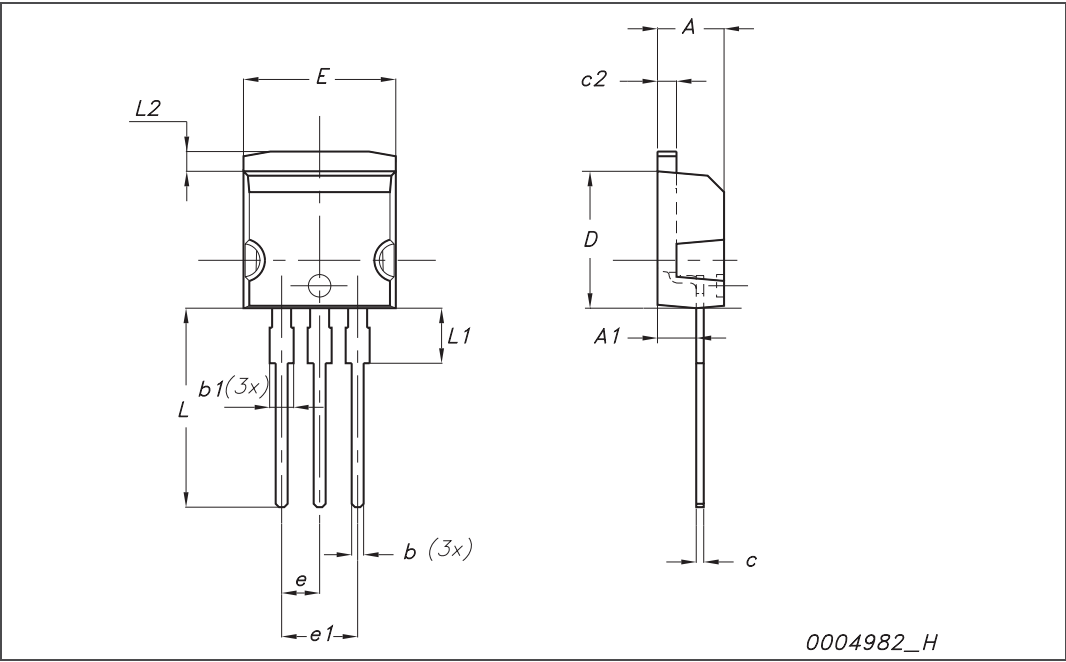
TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2



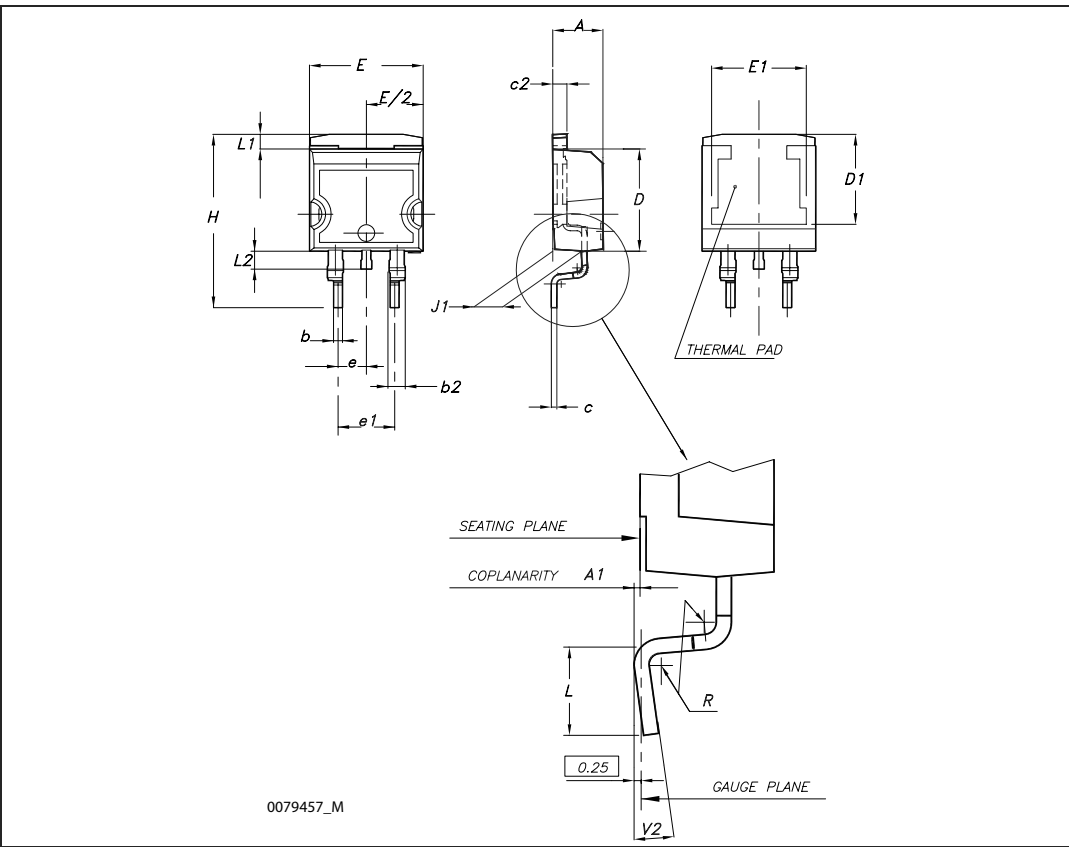
I²PAK (TO-262) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



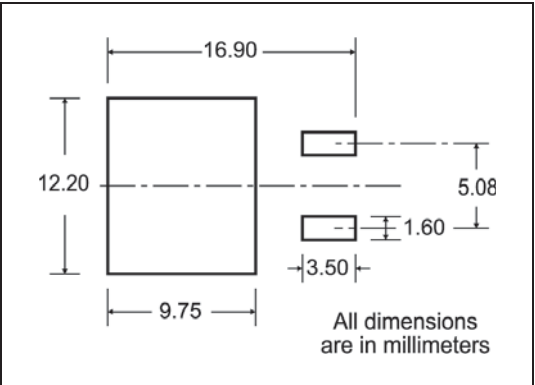
D²PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°

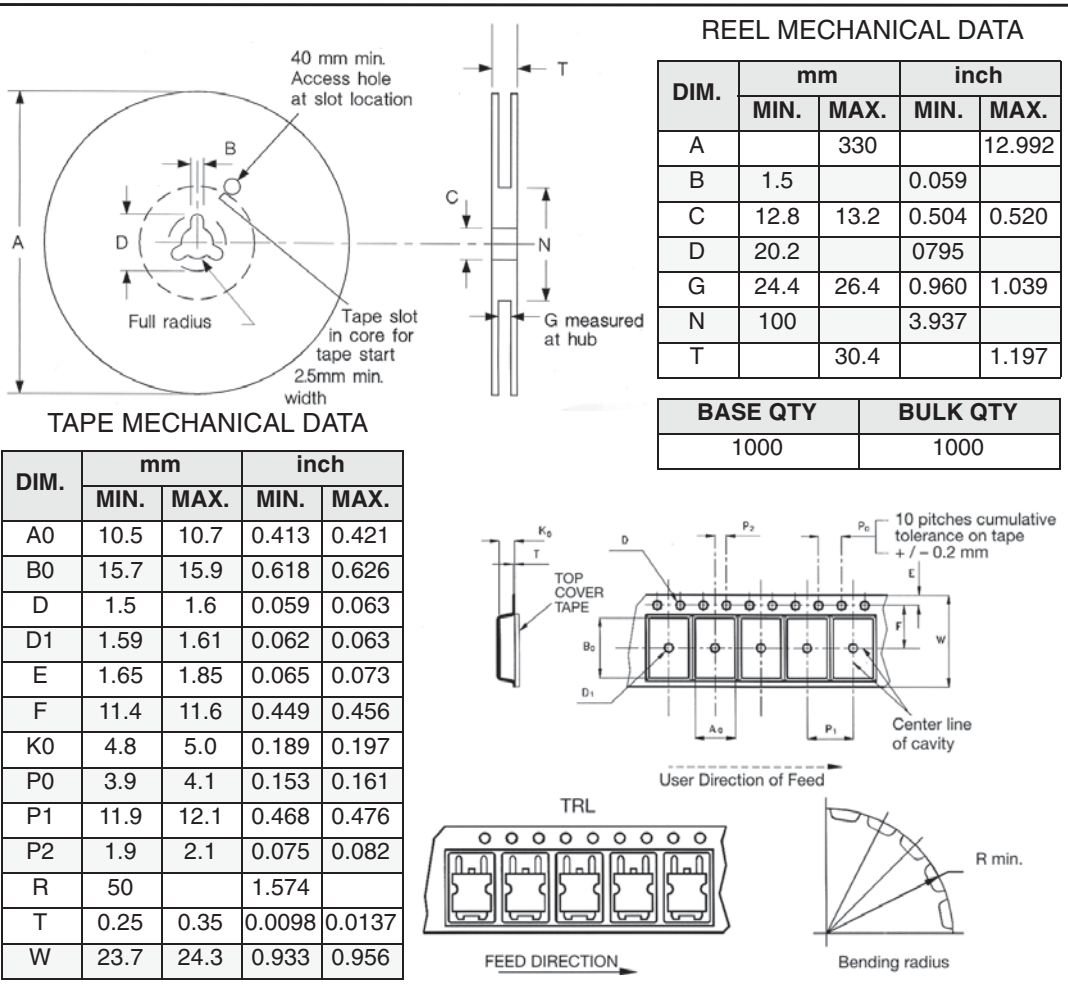


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 8. Document revision history

Date	Revision	Changes
16-Jan-2009	1	First release
15-May-2009	2	Updated figures 9 , 10 , 11 and 17
12-Jun-2009	3	Figure 15 has been updated

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